

Silicon PNP Power Transistors

MJ2955

DESCRIPTION

- With TO-3 package
- Complement to type MJ2955
- DC current gain $-h_{FE} = 20-70 @ I_C = 4 \text{ A}$
- Excellent safe operating area

APPLICATIONS

- Designed for general-purpose switching and amplifier applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

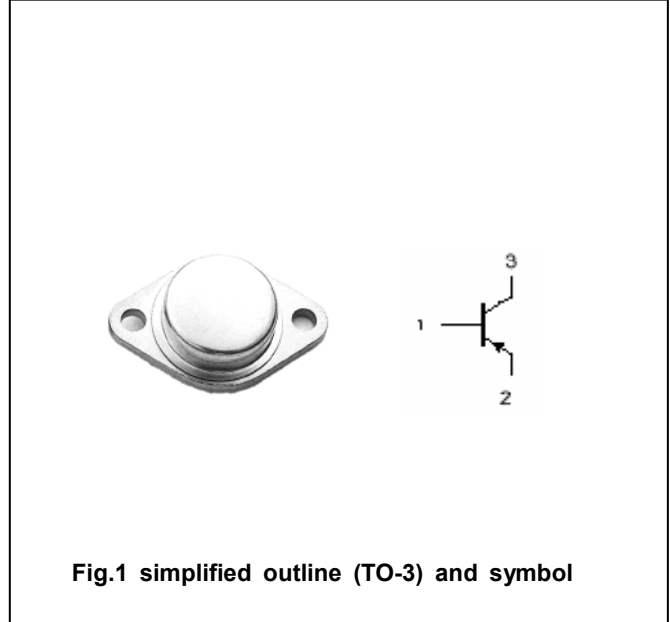


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-15	A
I_B	Base current		-7	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	115	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th j-c}$	Thermal resistance junction to case	1.52	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ; I _B =0	-60			V
V _{CER(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ; R _{BE} =100Ω	-70			V
V _{CE(sat)-1}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-1.1	V
V _{CE(sat)-2}	Collector-emitter saturation voltage	I _C =-10A ; I _B =-3.3A			-3.0	V
V _{BE}	Base-emitter on voltage	I _C =-4A ; V _{CE} =-4V			-1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =-30V ; I _B =0			-0.7	mA
I _{CEX}	Collector cut-off current	V _{CE} =-100V ; V _{BE(off)} =-1.5V T _C =150°C			-1.0 -5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V ; I _C =0			-5.0	mA
h _{FE-1}	DC current gain	I _C =-4A ; V _{CE} =-4V	20		70	
h _{FE-2}	DC current gain	I _C =-10A ; V _{CE} =-4V	5.0			
I _{S/b}	Second breakdown collector current With base forward biased	V _{CE} =-40Vdc, t=1.0s, Nonrepetitive	-2.87			A
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	2.5			MHz

PACKAGE OUTLINE

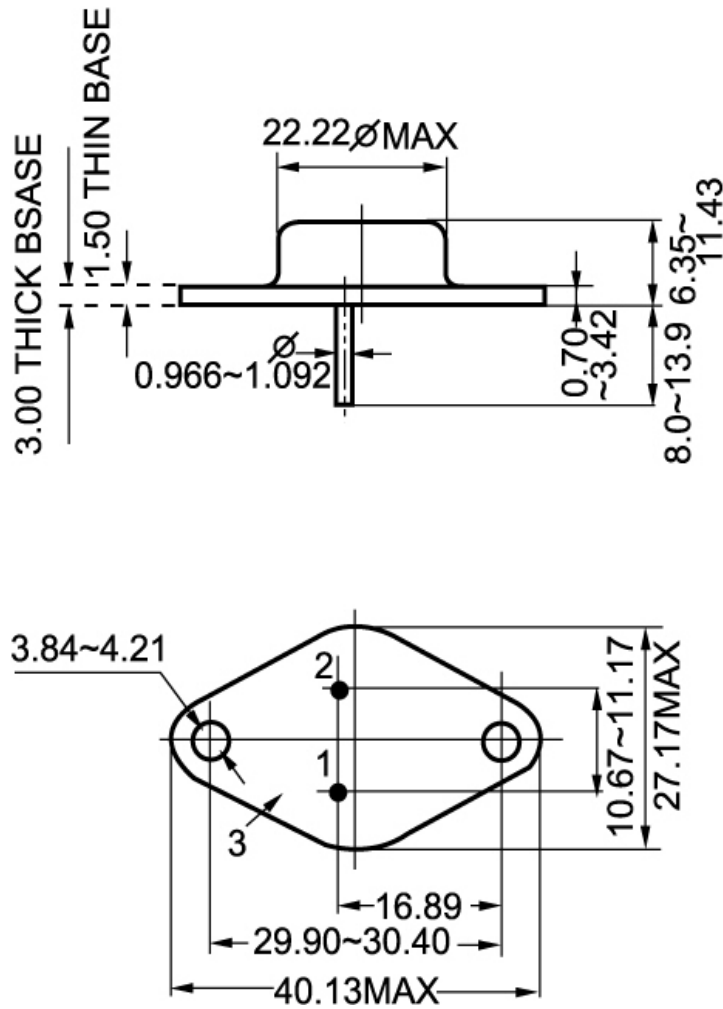


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)